Features

- Advanced Trench Cell Design
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free. “Green” Device (1)
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

P-CHANNEL MOSFET

Maximum Ratings

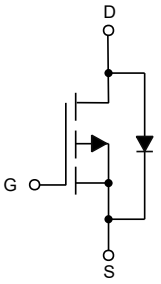
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance:103.1°C/W Junction to Ambient(Steady-State)(2)

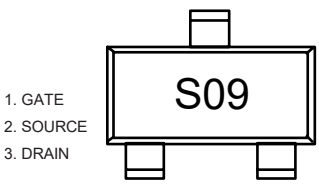
Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	-60	V
Gate-Source Volltage		V_{GS}	±20	V
Continuous Drain Current	T_A=25°C	I_D	-1.6	A
	T_A=100°C		-1.0	
Pulsed Drain Current(3)		I_{DM}	-8.0	A
Total Power Dissipation(4)		P_D	1.2	W

Note:

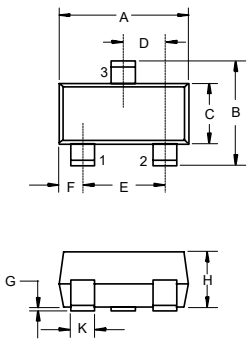
1. Halogen free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ t≤ 10s and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P_D is based on max. junction temperature, using junction to ambient thermal resistance.

Internal Structure and Marking Code



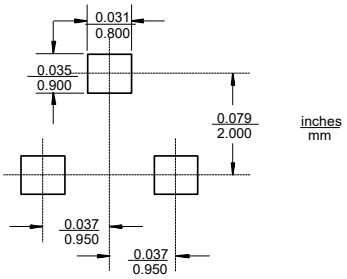


SOT-23



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.110	0.120	2.80	3.04	
B	0.090	0.104	2.30	2.64	
C	0.047	0.055	1.20	1.40	
D	0.034	0.041	0.85	1.05	
E	0.067	0.083	1.70	2.10	
F	0.018	0.024	0.45	0.60	
G	0.0004	0.004	0.01	0.10	
H	0.035	0.040	0.90	1.02	
J	0.003	0.007	0.08	0.18	
K	0.012	0.020	0.30	0.51	
L	0.007	0.020	0.20	0.50	

Suggested Solder Pad Layout



Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=-250μA	-60			V
Gate-Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-60V, V_{GS}=0V			-1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=-250μA	-1		-2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=-10V, I_D=-1.5A		120	160	mΩ
		V_{GS}=-4.5V, I_D=-1A		160	240	
Gate Resistance	R_g	F=1MHz, Open drain		5		Ω
Diode Characteristics						
Continuous Body Diode Current	I_S				-1.6	A
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=-1.5A			-1.2	V
Reverse Recovery Time	t_{rr}	I_F=-1.5A, dI_F/dt=100A/μs		18.1		ns
Reverse Recovery Charge	Q_{rr}			13		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=-30V,V_{GS}=0V,f=1MHz		429		pF
Output Capacitance	C_{oss}			34		
Reverse Transfer Capacitance	C_{rss}			27.5		
Total Gate Charge	Q_g	V_{DS}=-30V,V_{GS}=-10V,I_D=-1.5A		10.4		nC
Gate-Source Charge	Q_{gs}			1.4		
Gate-Drain Charge	Q_{gd}			2.6		
Turn-On Delay Time	$t_{d(on)}$	V_{DD}=-30V, V_{GS}=-10V, R_{GEN}=3Ω, I_{DS}=-1.5A		7		ns
Turn-On Rise Time	t_r			4		
Turn-Off Delay Time	$t_{d(off)}$			17		
Turn-Off Fall Time	t_f			5.9		

Curve Characteristics

Fig. 1 - Typical Output Characteristics

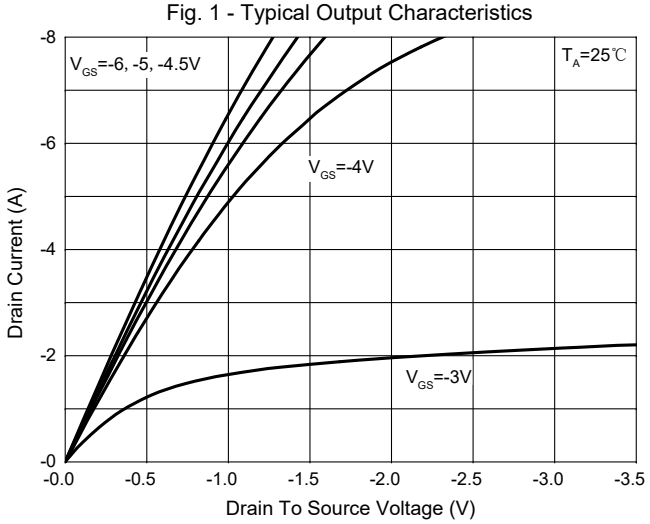


Fig. 2 - Transfer Characteristics

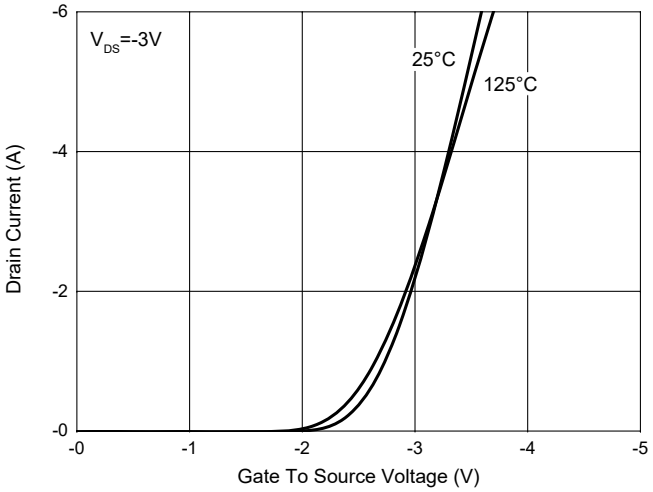


Fig. 3 - $R_{DS(ON)}$—I_D

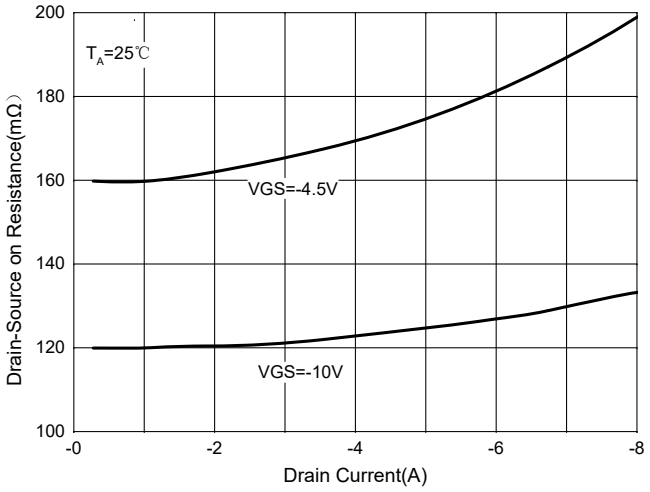


Fig. 4 - $R_{DS(ON)}$—V_{GS}

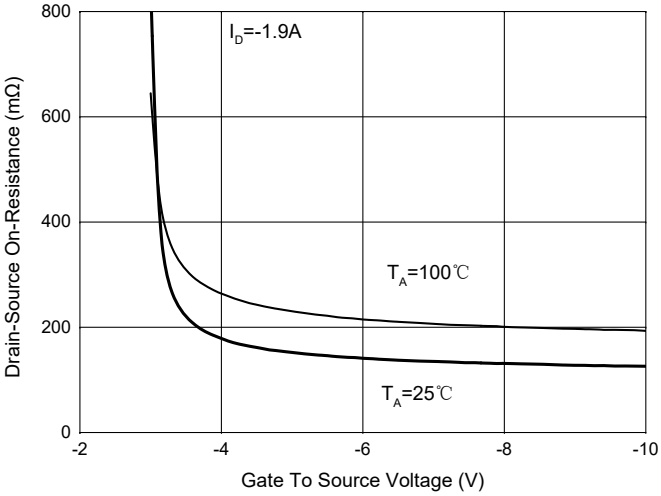


Fig. 5 - I_S—V_{SD}

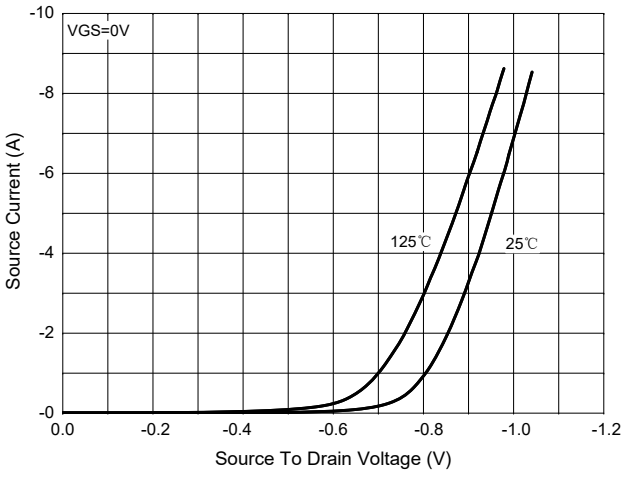
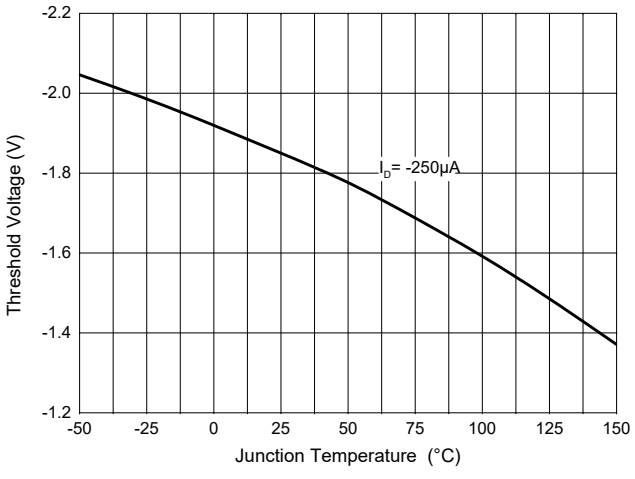


Fig. 6 - Threshold Voltage



Curve Characteristics

Fig. 7 - GateCharge

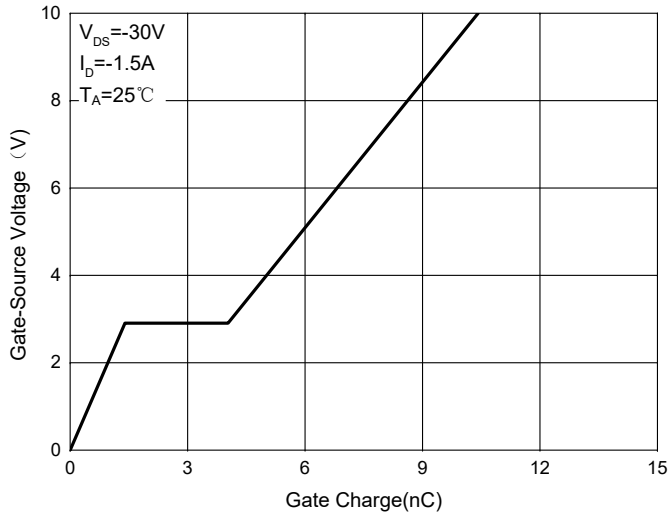


Fig.8-NormalizedOnResistanceCharacteristics

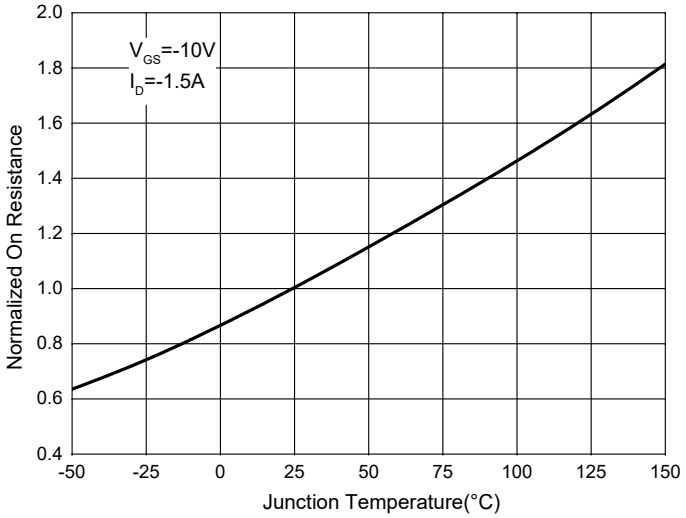


Fig. 9 - Capacitance Characteristics

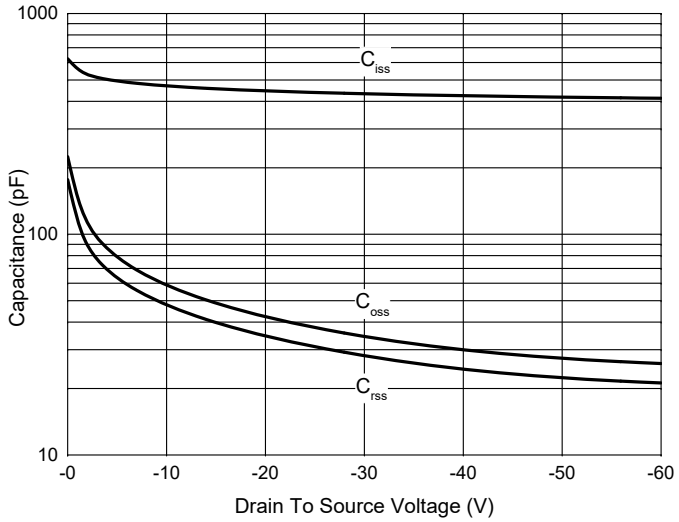


Fig. 10 - Current dissipation

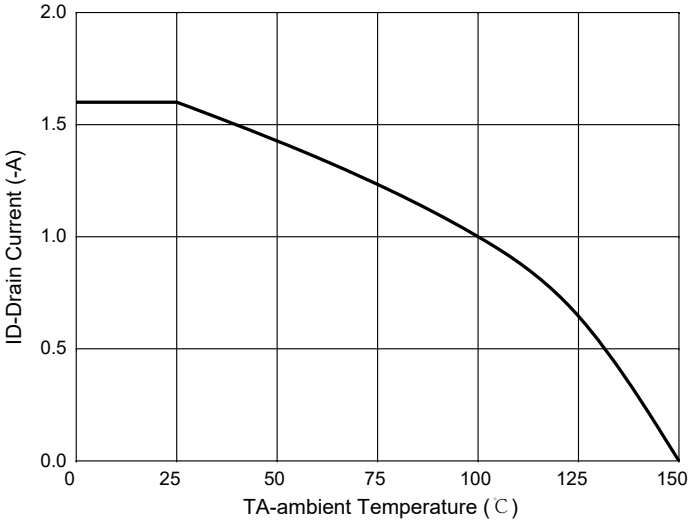
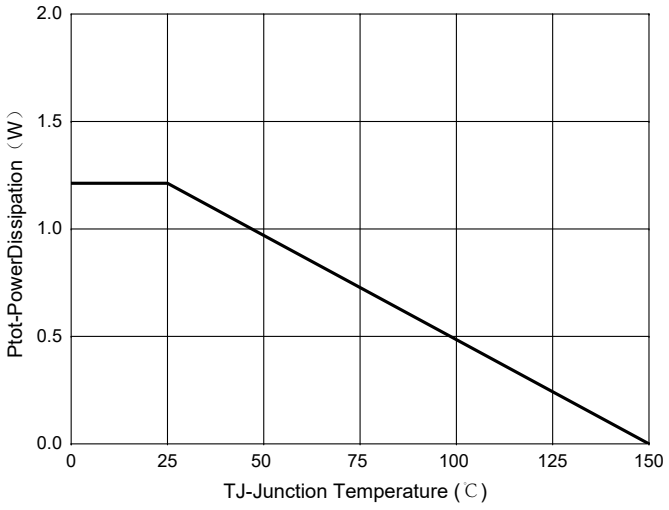


Fig.11-PowerDissipation



Curve Characteristics

Fig. 12 - Safe Operation Area

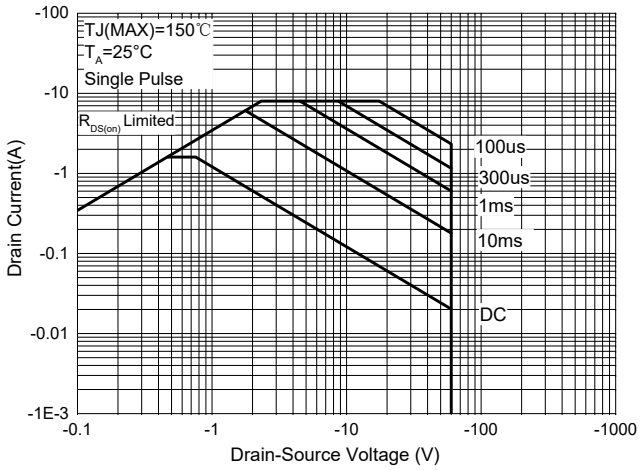
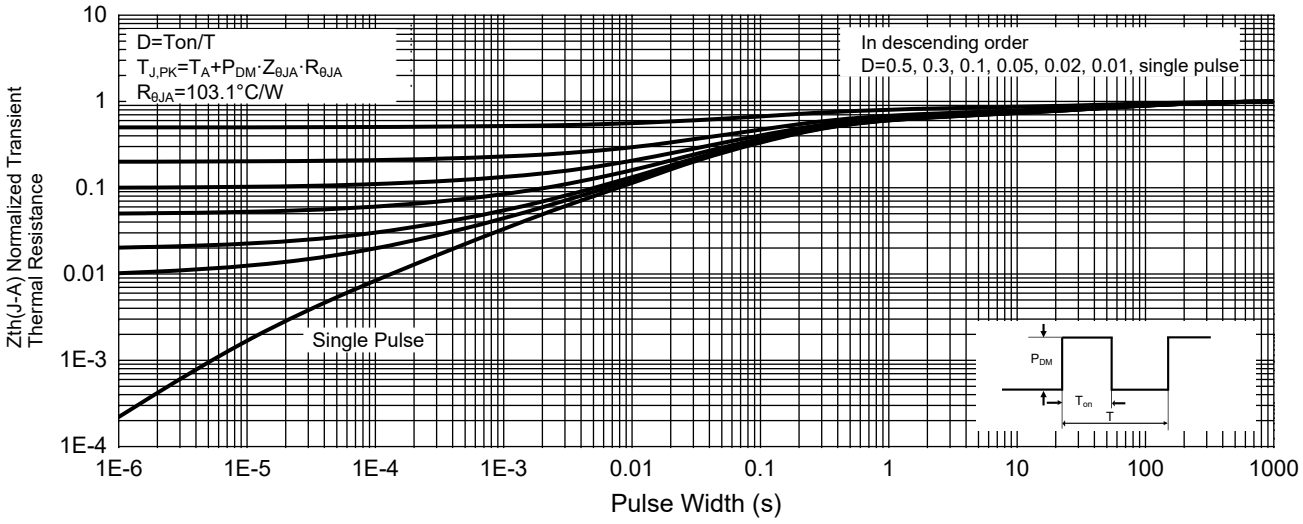


Fig. 13 -Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 3Kpcs/Reel
Part Number-13P	Tape&Reel: 10Kpcs/Reel

单击下面可查看定价，库存，交付和生命周期等信息

>>MCC(美微科)